



High-end Power Semiconductor Manufacturer

ZP800A 3800-4400V Standard Rectifier Diode

- High power cycling capability
- Low on-state and switching losses
- Optimized for line frequency rectifiers
- Designed for traction and industrial applications



Average forward current		I _{FAV}	800 A	
Repetitive peak reverse voltage		V _{RRM}	3800 – 4400 V	
V _{RRM} , V	3800	4000	4200	4400
Voltage code	38	40	42	44
T _j , °C	-60 – 150			

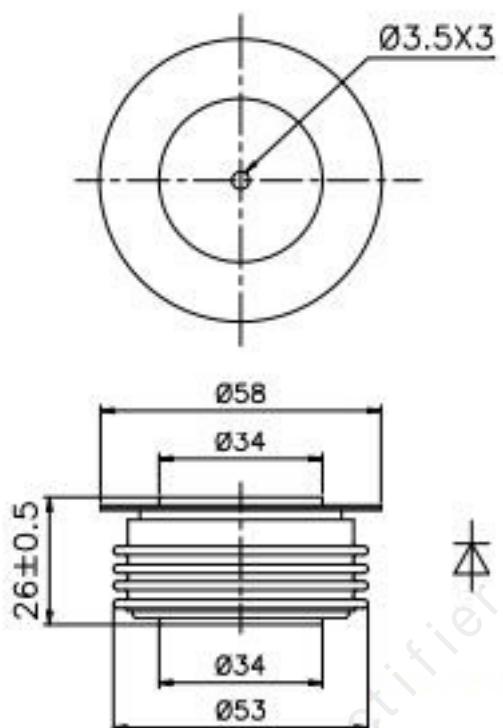
MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions
ON-STATE				
I _{FAV}	Average forward current	A	800	T _c =100 °C; Double side cooled; 180° half-sine wave; 50 Hz
I _{FRMS}	RMS forward current	A	1256	T _c =94 °C; Double side cooled; 180° half-sine wave; 50 Hz
I _{FSM}	Surge forward current	kA	12.5 14.0	T _j =T _j max T _j =25 °C 180° half-sine wave; 50 Hz (t _p =10 ms); single pulse; V _R =0 V;
			14.0 16.0	T _j =T _j max T _j =25 °C 180° half-sine wave; 60 Hz (t _p =8.3 ms); single pulse; V _R =0 V;
I ² t	Safety factor	A ² s·10 ³	780 980	T _j =T _j max T _j =25 °C 180° half-sine wave; 50 Hz (t _p =10 ms); single pulse; V _R =0 V;
			810 1060	T _j =T _j max T _j =25 °C 180° half-sine wave; 60 Hz (t _p =8.3 ms); single pulse; V _R =0 V;
BLOCKING				
V _{RRM}	Repetitive peak reverse voltages	V	3800–4400	T _{j min} < T _j < T _{j max} ; 180° half-sine wave; 50 Hz;
V _{RSM}	Non-repetitive peak reverse voltages	V	3900–4500	T _{j min} < T _j < T _{j max} ; 180° half-sine wave; 50 Hz;single pulse;
V _R	Reverse continuous voltages	V	0.75·V _{RRM}	T _j =T _j max;
THERMAL				
T _{stg}	Storage temperature	°C	-60–150	
T _j	Operating junction temperature	°C	-60–150	
MECHANICAL				
F	Mounting force	kN	14.0–16.0	
a	Acceleration	m/s ²	50 100	Device unclamped Device clamped

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V _{FM}	Peak forward voltage, max	V	1.97	T _j =25 °C; I _{FM} =2512 A	
V _{F(TO)}	Forward threshold voltage, max	V	1.02	T _j =T _{j max} ; 0.5 π I _{FAV} < I _T < 1.5 π I _{FAV}	
r _T	Forward slope resistance, max	mΩ	0.510		
BLOCKING					
I _{RRM}	Repetitive peak reverse current, max	mA	70	T _j =T _{j max} ; V _R =V _{RRM}	
THERMAL					
R _{thjc}	Thermal resistance, junction to case, max	°C/W	0.035	Direct current	Double side cooled
R _{thjc-A}			0.077		Anode side cooled
R _{thjc-K}			0.063		Cathode side cooled
R _{thck}	Thermal resistance, case to heatsink, max	°C/W	0.006	Direct current	
MECHANICAL					
w	Weight, typ	g	280		
D _s	Surface creepage distance	mm (inch)	33.30 (1.311)		
D _a	Air strike distance	mm (inch)	22.50 (0.886)		

OVERALL DIMENSIONS



ZT40

All dimensions in millimeters